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2N5770



NPN RF Transistor

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43. See PN918 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	4.5	V
Ic	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range -55 to +150		°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N5770	
P _D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

NPN RF Transistor

(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 3.0 \text{ mA}, I_B = 0$	15		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 1.0 \mu\text{A}, I_E = 0$	30		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	4.5		V
СВО	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, I_{E} = 0$		10	nA
I _{EBO}	Emitter Cutoff Current	$V_{CB} = 15 \text{ V}, I_E = 0, T_A = 150 ^{\circ}\text{C}$ $V_{EB} = 3.0 \text{ V}, I_C = 0$		1.0	μA μA
EBO	Emilia Guion Guneni	$V_{EB} = 0.0 \text{ V}, I_{C} = 0$		1.0	μA
ON CHAF	RACTERISTICS*				
h _{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 3.0 \text{ mA}$	20		
\ /	Collector-Emitter Saturation Voltage	$V_{CE} = 10 \text{ V}, I_{C} = 8.0 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$	50	200	V
V _{CE(sat)}	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		1.0	V
V BE(sat)	Dase Emitter Saturation Voltage	IC = 10 1101, IB = 1.0 1101		1.0	
					•
CMALL CI	CNAL CHADACTEDISTICS				
	GNAL CHARACTERISTICS	L10mA V80V		I 60	l dB
	GNAL CHARACTERISTICS Noise Figure	$I_C = 1.0 \text{ mA}, V_{CE} = 8.0 \text{ V},$ $f = 60 \text{ MHz}, Rg = 400 \Omega$		6.0	dB
NF		$f = 60 \text{ MHz}, Rg = 400 \Omega$ $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$	0.7	6.0	dB pF
NF C _{cb}	Noise Figure	$f = 60 \text{ MHz}, \text{ Rg} = 400 \Omega$	0.7		
NF C _{cb}	Noise Figure Collector-Base Capacitance	$\begin{split} &f = 60 \text{ MHz}, \text{ Rg} = 400 \Omega\\ &V_{\text{CB}} = 10 \text{ V}, \text{ I}_{\text{E}} = 0, \text{ f} = 1.0 \text{ MHz}\\ &V_{\text{EB}} = 0.5 \text{ V}\\ &I_{\text{C}} = 8.0 \text{ mA}, V_{\text{CE}} = 10 \text{ V}, \end{split}$		1.1	pF
NF C _{cb}	Noise Figure Collector-Base Capacitance Input Capacitance	$\begin{aligned} &f = 60 \text{ MHz}, & Rg = 400 \ \Omega \\ &V_{CB} = 10 \text{ V}, & I_{E} = 0, & f = 1.0 \text{ MHz} \\ &V_{EB} = 0.5 \text{ V} \end{aligned}$	9.0	1.1	pF
NF C _{cb} C _{ib}	Noise Figure Collector-Base Capacitance Input Capacitance Small-Signal Current Gain	$\begin{split} &f=60 \text{ MHz}, Rg=400 \Omega \\ &V_{CB}=10 V, I_E=0, f=1.0 \text{MHz} \\ &V_{EB}=0.5 V \\ &I_C=8.0 \text{mA}, V_{CE}=10 V, \\ &f=100 \text{MHz} \\ &I_C=8.0 \text{mA}, V_{CE}=10 V, \\ &f=1.0 \text{kHz} \end{split}$	9.0	1.1 2.0 18 240	pF pF
NF C _{cb} C _{ib}	Noise Figure Collector-Base Capacitance Input Capacitance	$\begin{split} &f=60 \text{ MHz}, Rg=400 \Omega \\ &V_{CB}=10 V, I_E=0, f=1.0 \text{MHz} \\ &V_{EB}=0.5 V \\ &I_C=8.0 \text{mA}, V_{CE}=10 V, \\ &f=100 \text{MHz} \\ &I_C=8.0 \text{mA}, V_{CE}=10 V, \end{split}$	9.0	1.1 2.0 18	pF
NF C _{cb} C _{ib}	Noise Figure Collector-Base Capacitance Input Capacitance Small-Signal Current Gain	$\begin{split} &f=60 \text{ MHz}, Rg=400 \Omega \\ &V_{CB}=10 V, I_{E}=0, f=1.0 \text{ MHz} \\ &V_{EB}=0.5 V \\ &I_{C}=8.0 \text{mA}, V_{CE}=10 V, \\ &f=100 \text{MHz} \\ &I_{C}=8.0 \text{mA}, V_{CE}=10 V, \\ &f=1.0 \text{kHz} \\ &I_{E}=8.0 \text{mA}, V_{CB}=10 V, \end{split}$	9.0	1.1 2.0 18 240	pF pF
NF C _{cb} Cib nfe	Noise Figure Collector-Base Capacitance Input Capacitance Small-Signal Current Gain	$\begin{split} &f=60 \text{ MHz}, Rg=400 \Omega \\ &V_{CB}=10 V, I_{E}=0, f=1.0 \text{ MHz} \\ &V_{EB}=0.5 V \\ &I_{C}=8.0 \text{mA}, V_{CE}=10 V, \\ &f=100 \text{MHz} \\ &I_{C}=8.0 \text{mA}, V_{CE}=10 V, \\ &f=1.0 \text{kHz} \\ &I_{E}=8.0 \text{mA}, V_{CB}=10 V, \end{split}$	9.0	1.1 2.0 18 240	pF pF
NF Cob Cib Ofe	Noise Figure Collector-Base Capacitance Input Capacitance Small-Signal Current Gain Collector-Base Time Constant	$\begin{split} &f=60 \text{ MHz}, Rg=400 \Omega \\ &V_{CB}=10 V, I_{E}=0, f=1.0 \text{MHz} \\ &V_{EB}=0.5 V \\ &I_{C}=8.0 \text{mA}, V_{CE}=10 V, \\ &f=100 \text{MHz} \\ &I_{C}=8.0 \text{mA}, V_{CE}=10 V, \\ &f=1.0 \text{kHz} \\ &I_{E}=8.0 \text{mA}, V_{CB}=10 V, \\ &f=79.8 \text{MHz} \\ \end{split}$	9.0	1.1 2.0 18 240	pF pF
NF Cob Cib Tre to 'Co FUNCTIO	Noise Figure Collector-Base Capacitance Input Capacitance Small-Signal Current Gain Collector-Base Time Constant	$\begin{split} &f=60 \text{ MHz}, Rg=400 \Omega \\ &V_{CB}=10 V, I_{E}=0, f=1.0 \text{MHz} \\ &V_{EB}=0.5 V \\ &I_{C}=8.0 \text{mA}, V_{CE}=10 V, \\ &f=100 \text{MHz} \\ &I_{C}=8.0 \text{mA}, V_{CE}=10 V, \\ &f=1.0 \text{kHz} \\ &I_{E}=8.0 \text{mA}, V_{CB}=10 V, \\ &f=79.8 \text{MHz} \end{split}$	9.0 40 3.0	1.1 2.0 18 240	pF pF

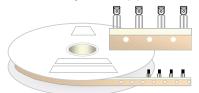
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

TO-92 Tape and Reel Data FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVR/418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z 2,000 Е D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** $\begin{array}{ll} \mbox{Unit weight} & = 0.22 \mbox{ gm} \\ \mbox{Reel weight with components} & = 1.04 \mbox{ kg} \\ \mbox{Ammo weight with components} & = 1.02 \mbox{ kg} \\ \mbox{Max quantity per intermediate box} & = 10,000 \mbox{ units} \end{array}$ Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** TO-92 STANDARD STRAIGHT FOR: PKG 92, 94 (NON PROELECTRON NO EOL NO LEADCLIP 2.0 K / BOX SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

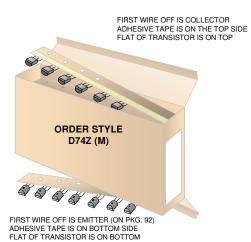


Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

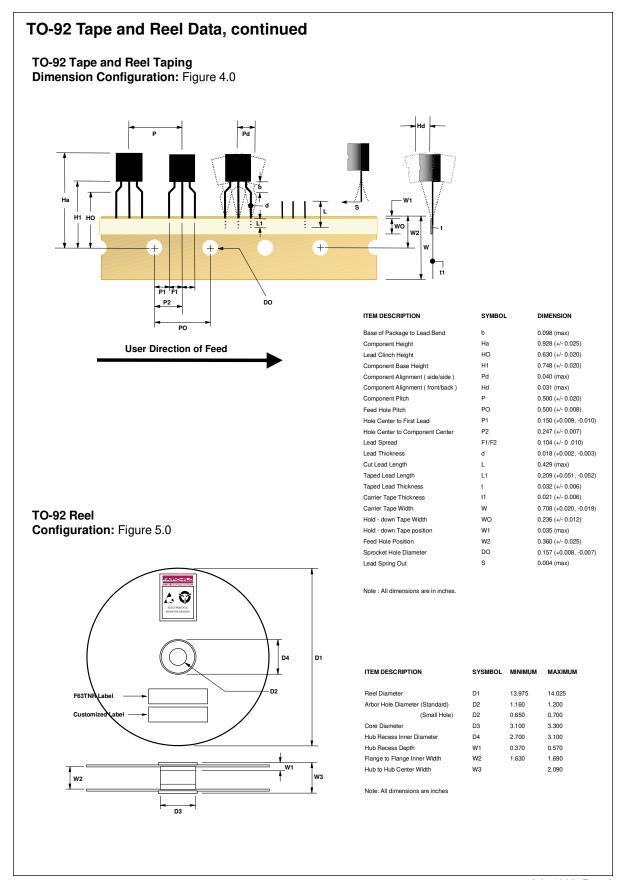
Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





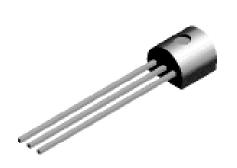
FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

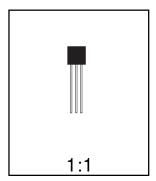


TO-92 Package Dimensions



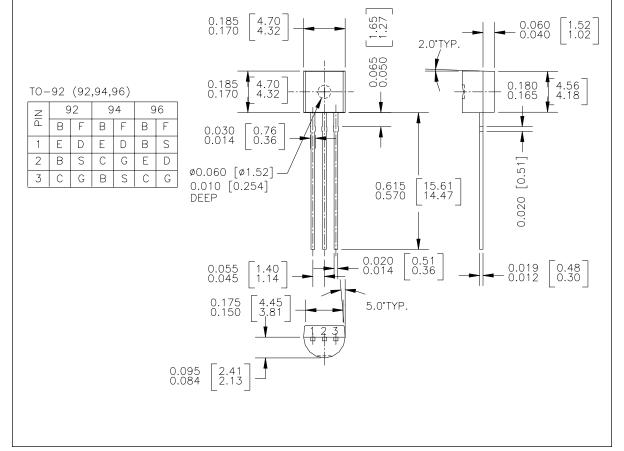
TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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